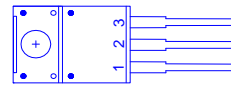
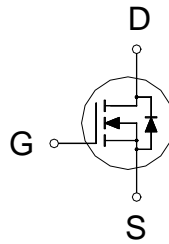




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
600V	1.3Ω	6A



- 1. GATE
- 2. DRAIN
- 3. SOURCE

ABSOLUTE MAXIMUM RATINGS(T_A=25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current ²	$T_C = 25\text{ °C}$	I_D	6	A
	$T_C = 100\text{ °C}$		3.8	
Pulsed Drain Current ¹		I_{DM}	20	
Avalanche Current ³		I_{AS}	3.5	
Avalanche Energy ³		EAS	61.2	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	32	W
	$T_C = 100\text{ °C}$		13	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3.8	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W

¹Pulse width limited by maximum junction temperature.

²Ensure that the channel temperature does not exceed 150°C.

³ $V_{DD} = 50V$, $L = 10mH$,starting $T_j = 25\text{ °C}$.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 30V$			±100	nA
Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_C = 25\text{ °C}$			1	μA
		$V_{DS} = 480V, V_{GS} = 0V, T_C = 100\text{ °C}$			10	

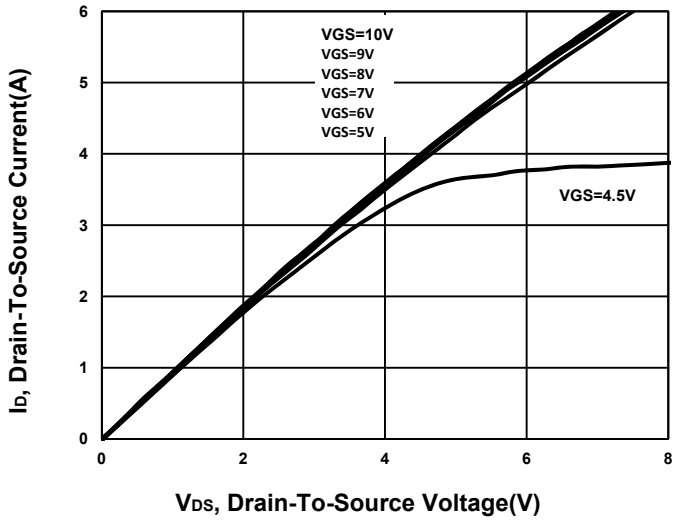
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3A$		1	1.3	Ω
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 3A$		10		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		953		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			18		
Total Gate Charge ²	Q_g	$V_{DD} = 480V, I_D = 6A, V_{GS} = 10V$		34		nC
Gate-Source Charge ²	Q_{gs}			4.4		
Gate-Drain Charge ²	Q_{gd}			14		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DD} = 300V, I_D = 6A, R_G = 25\Omega$		40		nS
Rise Time ²	t_r			33		
Turn-Off Delay Time ²	$t_{d(off)}$			130		
Fall Time ²	t_f			45		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$)						
Continuous Current ³	I_S				6	A
Forward Voltage ¹	V_{SD}	$I_F = 6A, V_{GS} = 0V$			1	V
Reverse Recovery Time	t_{rr}	$I_F = 6A, di_F/dt = 100A / \mu S$		362		nS
Reverse Recovery Charge	Q_{rr}			3		uC

¹Pulse test : Pulse Width $\leq 380\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.

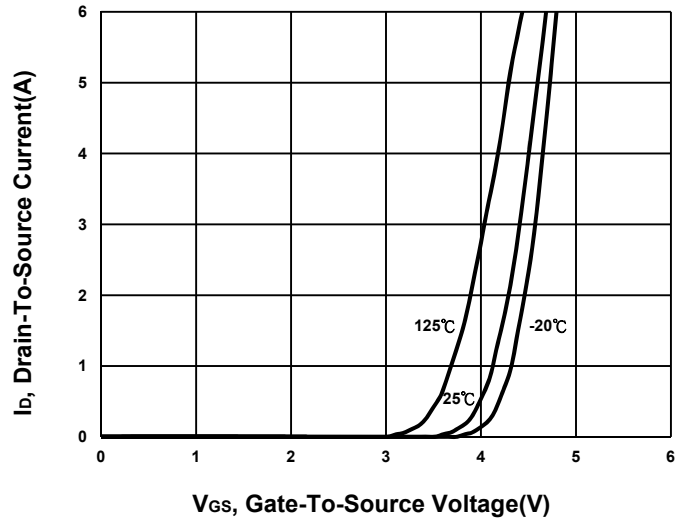
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

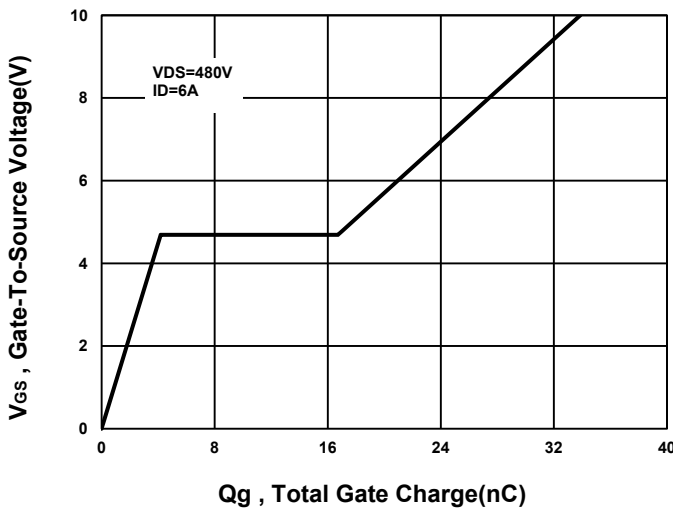
Output Characteristics



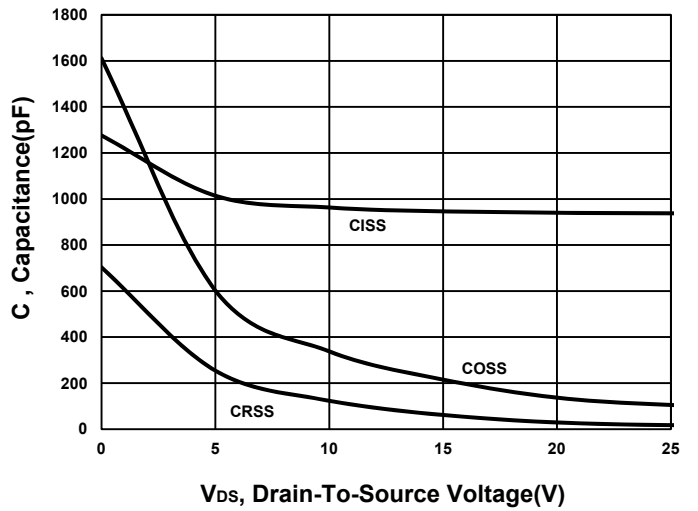
Transfer Characteristics



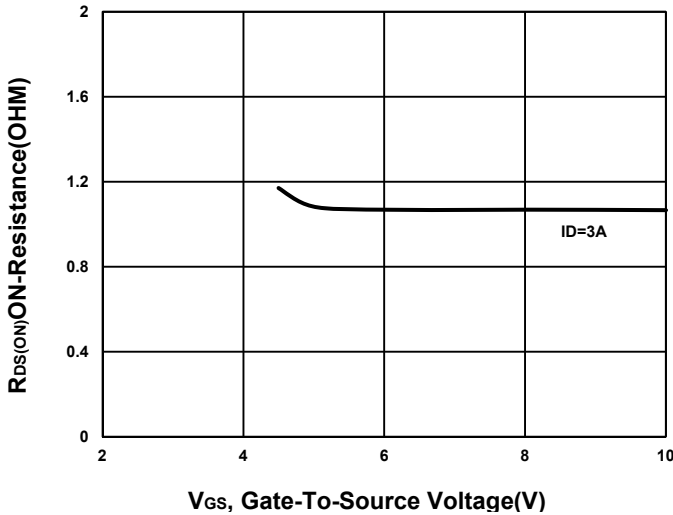
Gate charge Characteristics



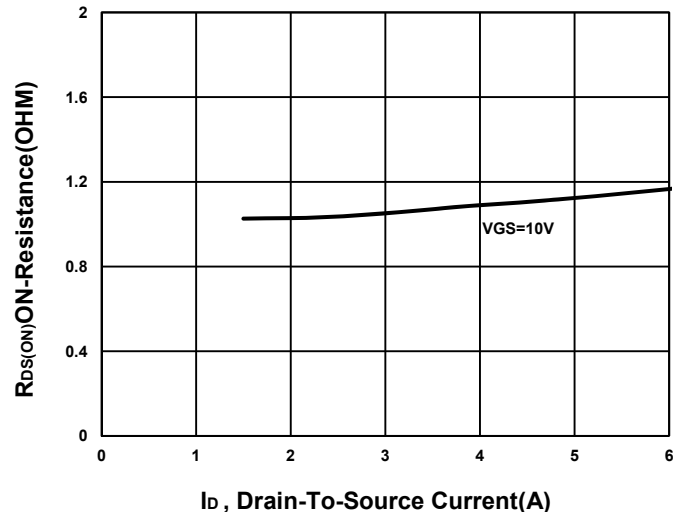
Capacitance Characteristic



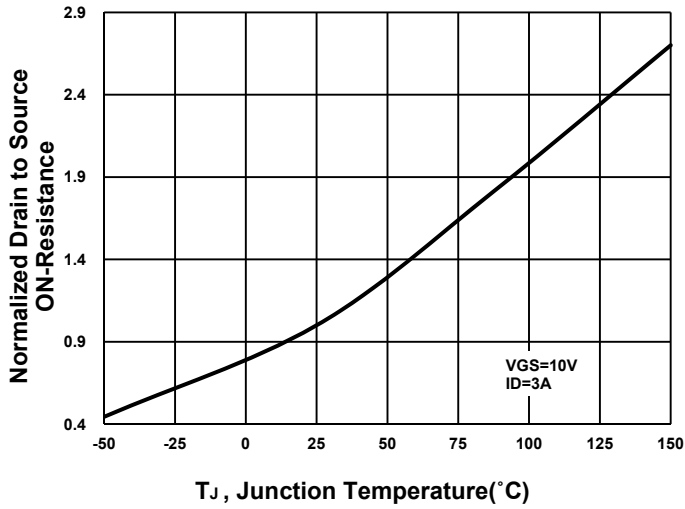
On-Resistance VS Gate-To-Source



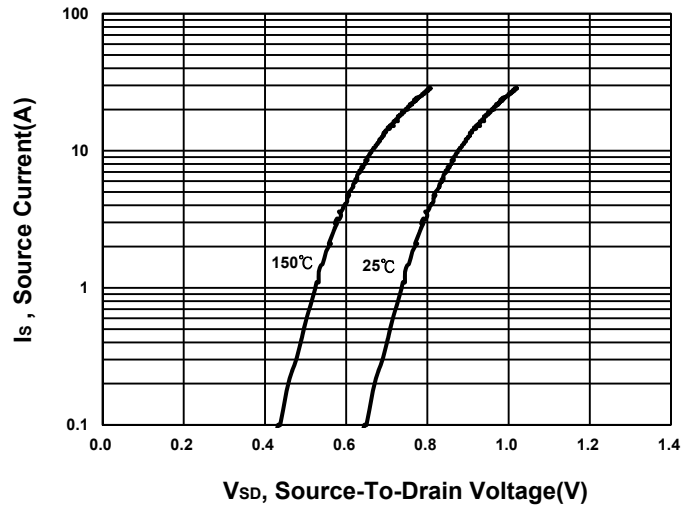
On-Resistance VS Drain Current



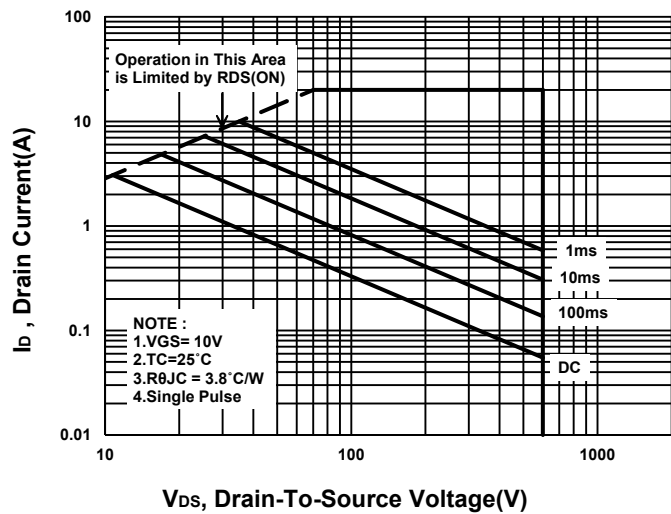
On-Resistance VS Temperature



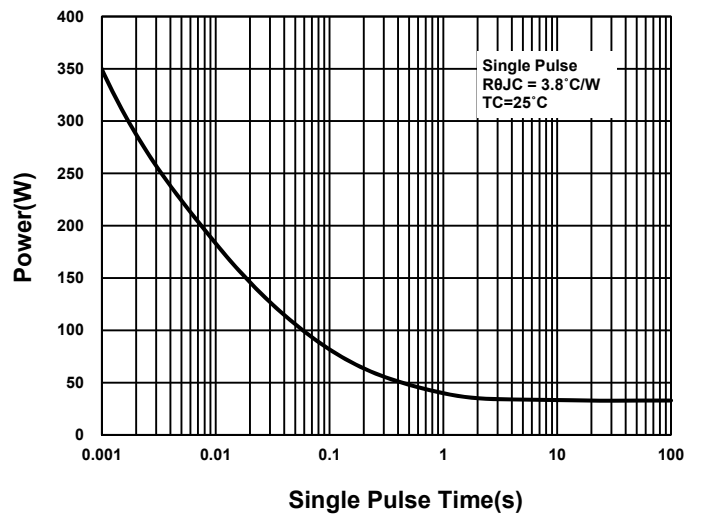
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

